

Application No. 10/595,640

July 18, 2008

Reply to the Office Action dated February 5, 2008 and  
the Advisory Action dated June 4, 2008

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**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claim 1 (currently amended): A liquid crystal display device comprising;

[[A]]a transistor-comprising including:

a source electrode and a drain electrode arranged in mutually opposing relation;

a semiconductor film comprising at least one layer disposed between the source electrode and the drain electrode;

a gate electrode disposed in adjacent relation to the semiconductor film;  
and

a gate insulating film disposed between the gate electrode and each of the source electrode, the drain electrode, and the semiconductor film; wherein

a concentration of fluorine contained in the gate insulating film is in a range of about 7 x 10<sup>18</sup> atoms/cm<sup>3</sup> to about 1 x 10<sup>20</sup> atoms/cm<sup>3</sup>-or-less;

the transistor is of an inverted stagger type in which the gate insulating film and the semiconductor film are formed in that order and the semiconductor film is disposed on the gate insulating film;-and

the gate insulating film is an amorphous silicon nitride film; and  
the transistor defines a switching element for a pixel electrode portion.

Claim 2 (currently amended): The transistor-liquid crystal display device of claim 1, wherein the concentration of the contained fluorine is in a range of about 7 x 10<sup>18</sup> atoms/cm<sup>3</sup> to about 1 x 10<sup>19</sup> atoms/cm<sup>3</sup>-or-less.

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Claim 3 (currently amended): The transistor-liquid crystal display device of claim 1, wherein the transistor which is of a field-effect type.

Claim 4 (canceled).

Claim 5 (currently amended): The transistor-liquid crystal display device of claim 1, wherein the gate insulating film is deposited by a CVD method.

Claims 6-8 (canceled).